

IRF7842PbF

HEXFET® Power MOSFET

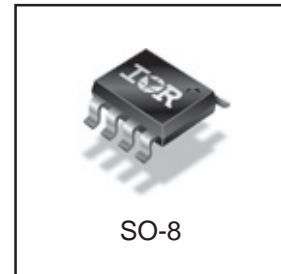
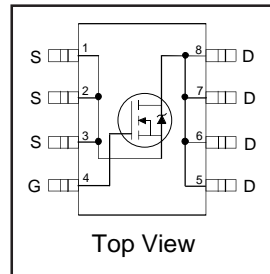
Applications

- Synchronous MOSFET for Notebook Processor Power
- Secondary Synchronous Rectification for Isolated DC-DC Converters
- Synchronous Fet for Non-Isolated DC-DC Converters
- Lead-Free

Benefits

- Very Low $R_{DS(on)}$ at 4.5V V_{GS}
- Low Gate Charge
- Fully Characterized Avalanche Voltage and Current

V_{DSS}	$R_{DS(on)}$ max	Q_g (typ.)
40V	5.0m Ω @ $V_{GS} = 10V$	33nC



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	40	V
V_{GS}	Gate-to-Source Voltage	± 20	
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	18	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	14	
I_{DM}	Pulsed Drain Current ①	140	
$P_D @ T_A = 25^\circ C$	Power Dissipation ④	2.5	W
$P_D @ T_A = 70^\circ C$	Power Dissipation ④	1.6	
	Linear Derating Factor	0.02	W/ $^\circ C$
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	$^\circ C$

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead ⑤	—	20	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient ④⑤	—	50	

Notes ① through ⑤ are on page 9

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Static @ T_J = 25°C (unless otherwise specified)

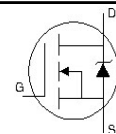
	Parameter	Min.	Typ.	Max.	Units	Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	40	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.037	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	4.0	5.0	mΩ	V _{GS} = 10V, I _D = 17A ③
		—	4.7	5.9		V _{GS} = 4.5V, I _D = 14A ③
V _{GS(th)}	Gate Threshold Voltage	1.35	—	2.25	V	V _{DS} = V _{GS} , I _D = 250μA
ΔV _{GS(th)}	Gate Threshold Voltage Coefficient	—	- 5.6	—	mV/°C	
I _{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	V _{DS} = 32V, V _{GS} = 0V
		—	—	150		V _{DS} = 32V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -20V
g _{fs}	Forward Transconductance	81	—	—	S	V _{DS} = 20V, I _D = 14A
Q _g	Total Gate Charge	—	33	50	nC	V _{DS} = 20V V _{GS} = 4.5V I _D = 14A
Q _{gs1}	Pre-V _{th} Gate-to-Source Charge	—	9.6	—		
Q _{gs2}	Post-V _{th} Gate-to-Source Charge	—	2.8	—		
Q _{gd}	Gate-to-Drain Charge	—	10	—		
Q _{godr}	Gate Charge Overdrive	—	10.6	—		
Q _{sw}	Switch Charge (Q _{gs2} + Q _{gd})	—	12.8	—		
Q _{oss}	Output Charge	—	18	—	nC	V _{DS} = 16V, V _{GS} = 0V
R _G	Gate Resistance	—	1.3	TBD	Ω	
t _{d(on)}	Turn-On Delay Time	—	14	—	ns	V _{DD} = 20V, V _{GS} = 4.5V ③ I _D = 14A Clamped Inductive Load
t _r	Rise Time	—	12	—		
t _{d(off)}	Turn-Off Delay Time	—	21	—		
t _f	Fall Time	—	5.0	—		
C _{iss}	Input Capacitance	—	4500	—	pF	V _{GS} = 0V V _{DS} = 20V f = 1.0MHz
C _{oss}	Output Capacitance	—	680	—		
C _{riss}	Reverse Transfer Capacitance	—	310	—		

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E _{AS}	Single Pulse Avalanche Energy ②	—	50	mJ
I _{AR}	Avalanche Current ①	—	14	A

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	3.1	A	MOSFET symbol showing the integral reverse p-n junction diode.
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	140		
V _{SD}	Diode Forward Voltage	—	—	1.0	V	T _J = 25°C, I _S = 14A, V _{GS} = 0V ③
t _{rr}	Reverse Recovery Time	—	99	150	ns	T _J = 25°C, I _F = 14A, V _{DD} = 20V
Q _{rr}	Reverse Recovery Charge	—	11	17	nC	di/dt = 100A/μs ③



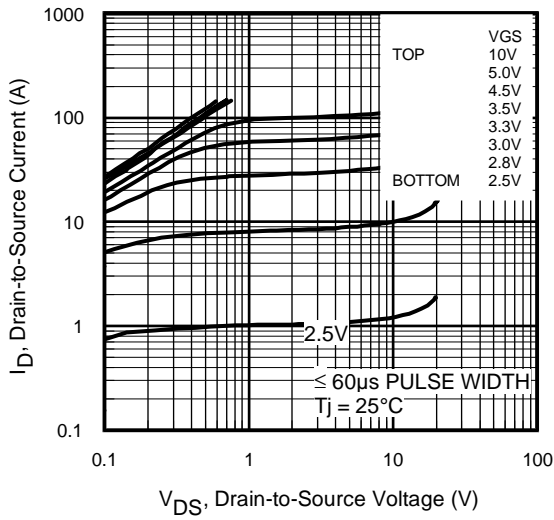


Fig 1. Typical Output Characteristics

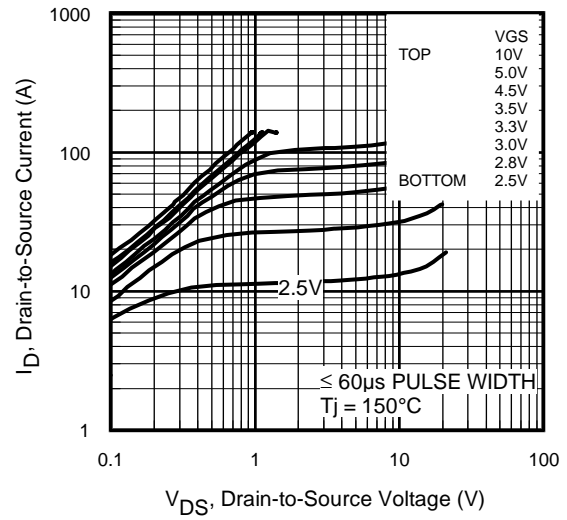


Fig 2. Typical Output Characteristics

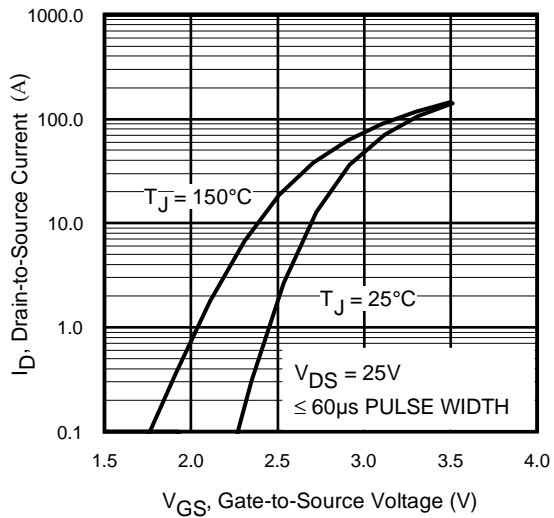


Fig 3. Typical Transfer Characteristics

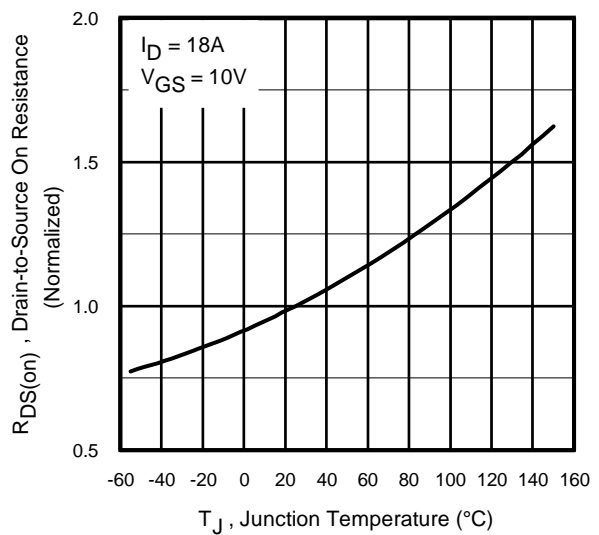


Fig 4. Normalized On-Resistance Vs. Temperature

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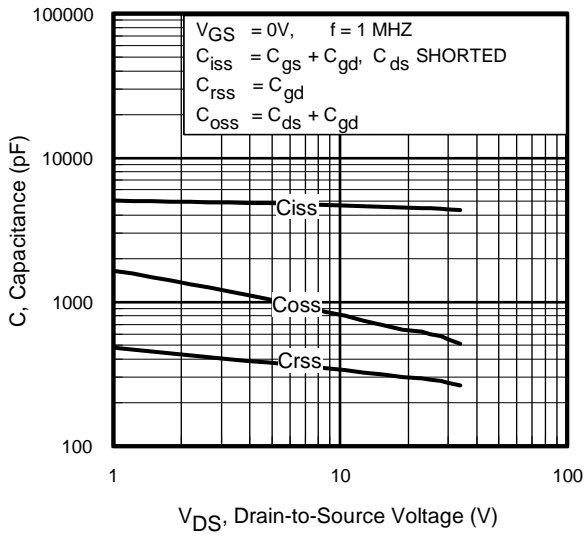


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

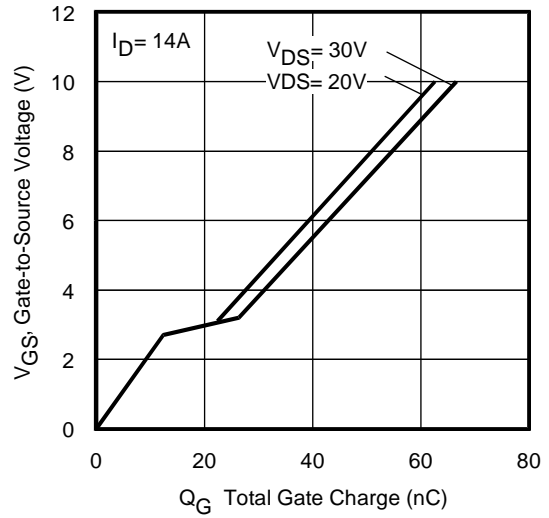


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

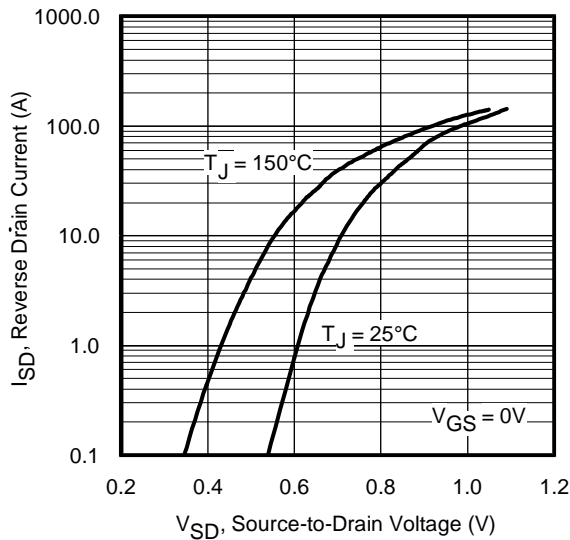


Fig 7. Typical Source-Drain Diode Forward Voltage

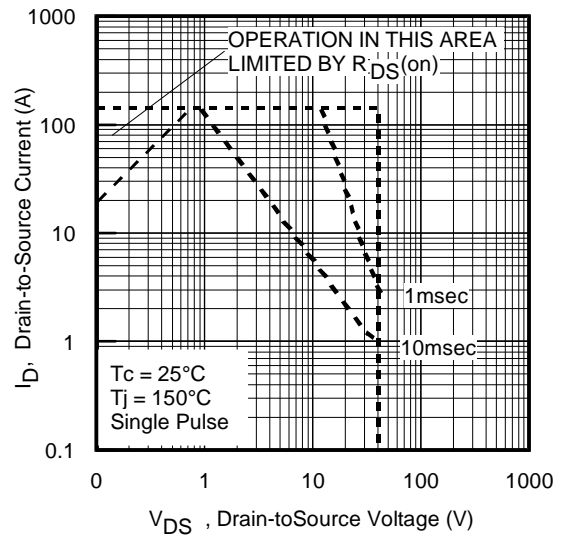


Fig 8. Maximum Safe Operating Area

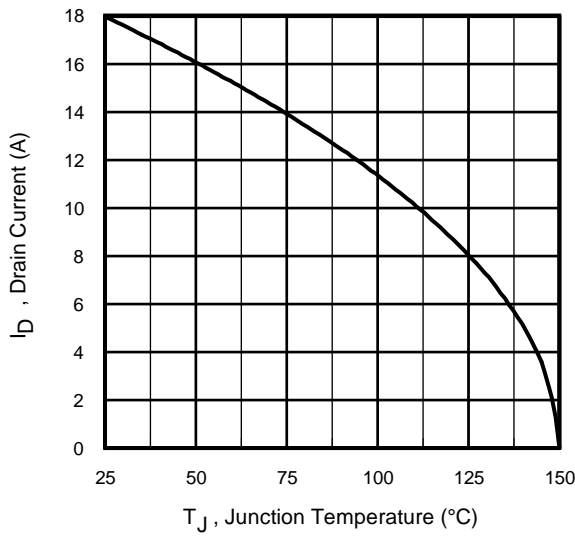


Fig 9. Maximum Drain Current Vs. Case Temperature

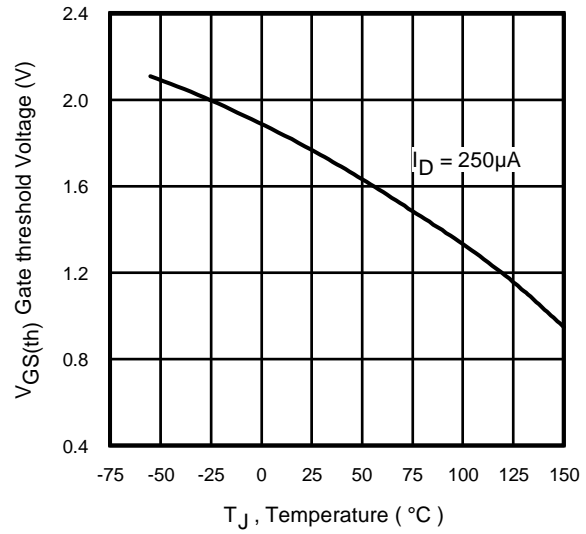


Fig 10. Threshold Voltage Vs. Temperature

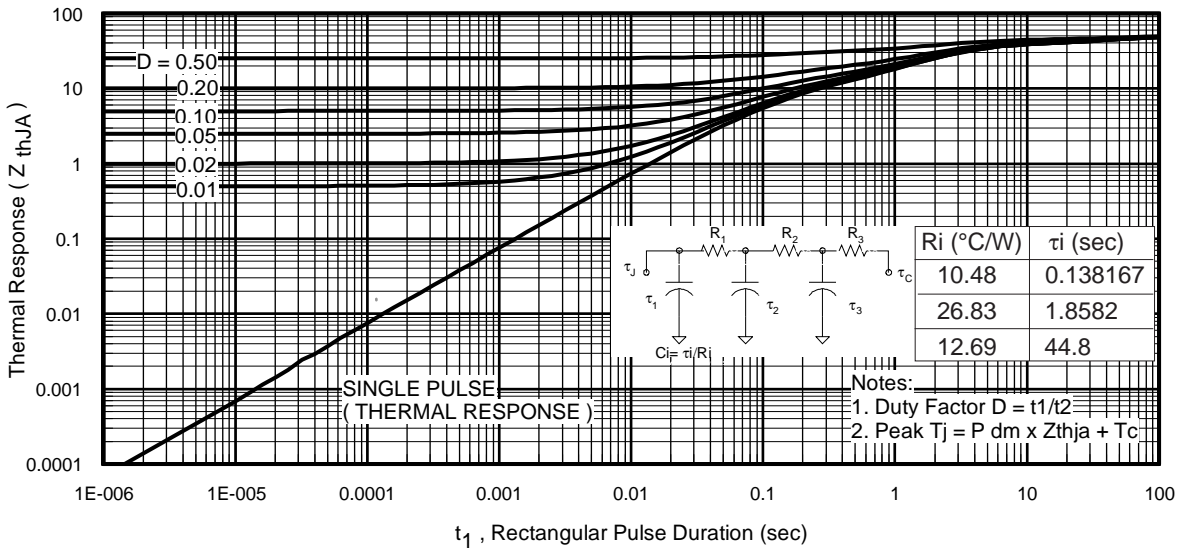


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

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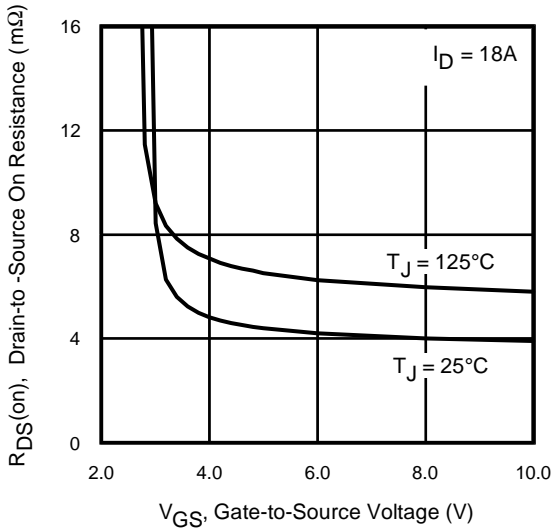


Fig 12. On-Resistance Vs. Gate Voltage

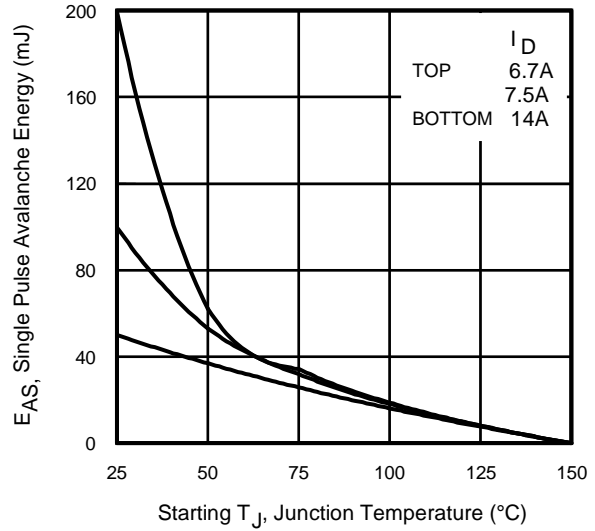


Fig 13c. Maximum Avalanche Energy Vs. Drain Current

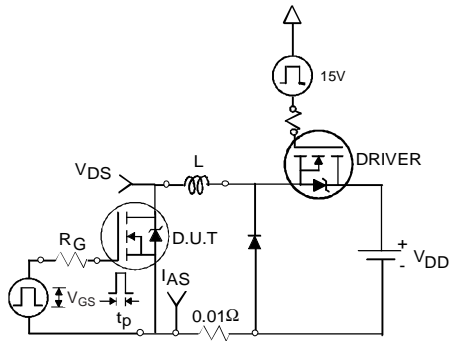


Fig 13a. Unclamped Inductive Test Circuit

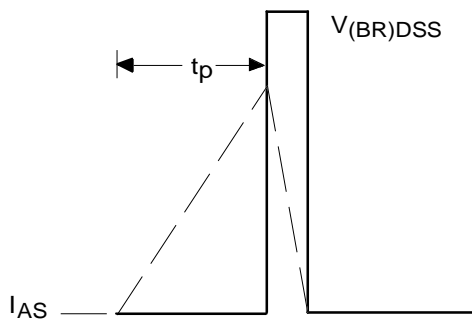


Fig 13b. Unclamped Inductive Waveforms

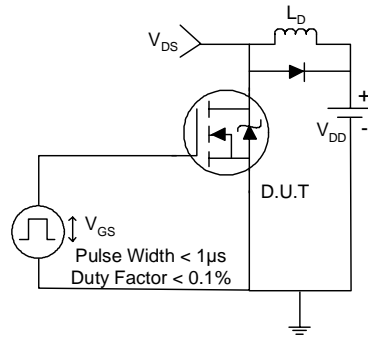


Fig 14a. Switching Time Test Circuit

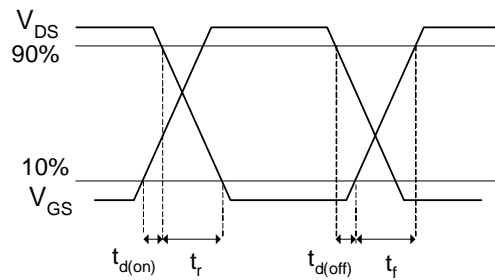
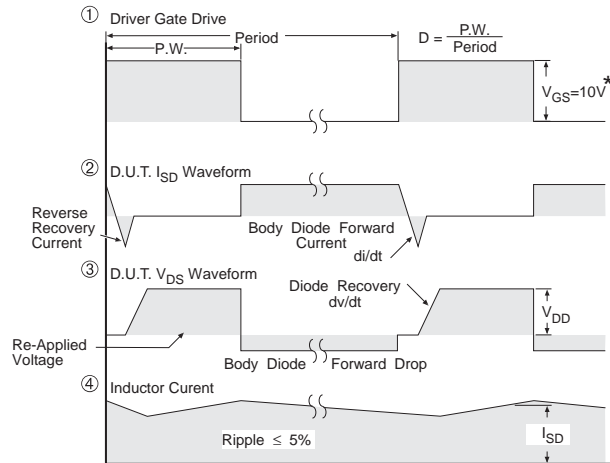
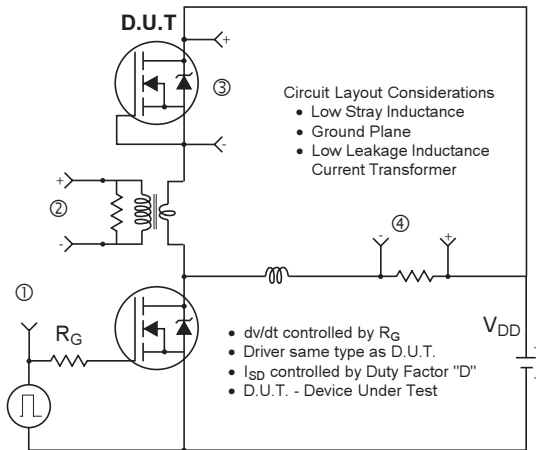


Fig 14b. Switching Time Waveforms

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* $V_{GS} = 5V$ for Logic Level Devices

Fig 15. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETS

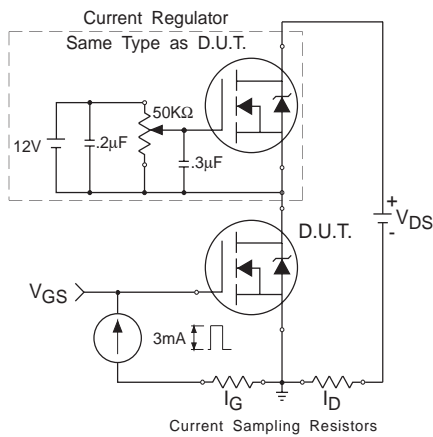


Fig 16. Gate Charge Test Circuit

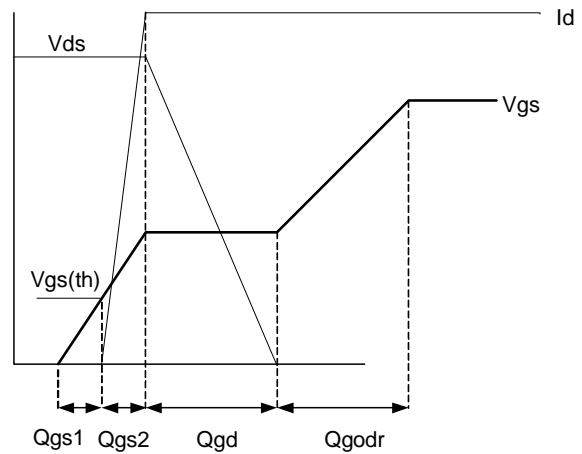
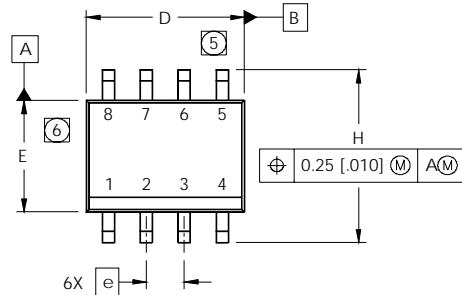


Fig 17. Gate Charge Waveform

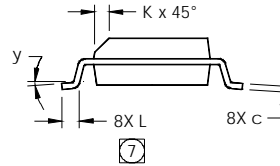
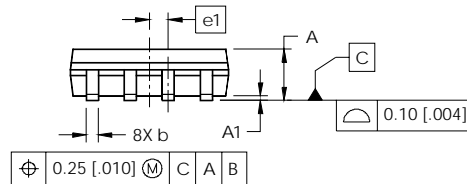
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SO-8 Package Outline

Dimensions are shown in millimeters (inches)



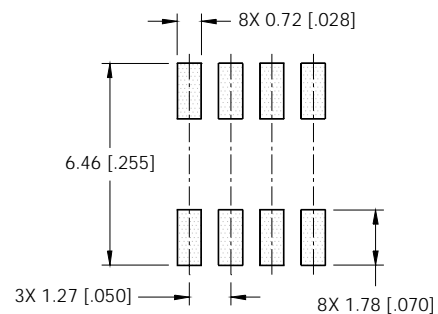
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



NOTES:

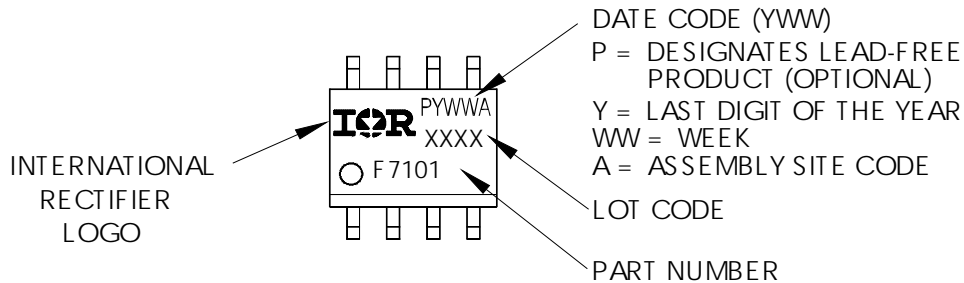
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [0.006].
- ⑥ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [0.010].
- ⑦ DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

FOOTPRINT



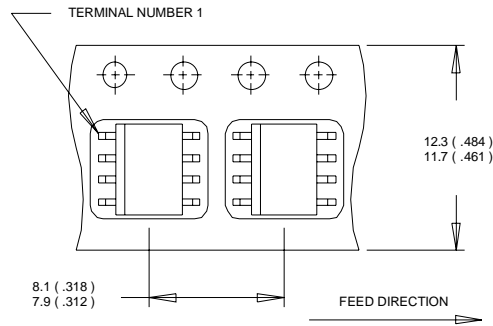
SO-8 Part Marking

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

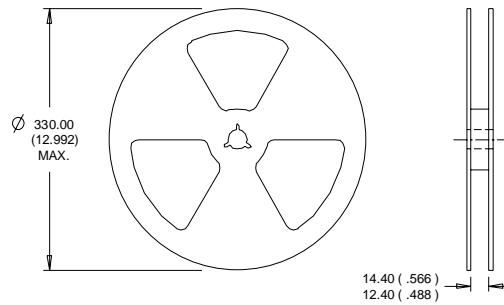


SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 0.5\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = 14\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ When mounted on 1 inch square copper board
- ⑤ R_θ is measured at T_J approximately 90°C

Data and specifications subject to change without notice.
 This product has been designed and qualified for the Consumer market.
 Qualifications Standards can be found on IR's Web site.